Transys Electronics LIMITED

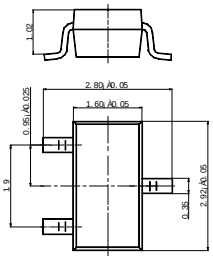
SOT-23-3L Plastic-Encapsulated Transistors

2SA812 TRANSISTOR (PNP)

SOT-23-3L

1. BASE
2. EMITTER
3. COLLECTOR





FEATURES

Power dissipation

P_{CM} : 0.2 W (Tamb=25℃)

Collector current

I_{CM} : -0.1 A

Collector-base voltage

$V_{(BR)CBO}$: -60 V

Operating and storage junction temperature range

T_J, T_{stg}: -55℃ to +150℃

ELECTRICAL CHARACTERISTICS (Tamb=25℃ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	Ic=-100μA, I_E=0	-60			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	Ic= -1mA, I_B=0	-50			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	I_E= -100μA, I_C=0	-5			V
Collector cut-off current	I_{CBO}	V_{CB}=- 60 V , I_E=0			-0.1	μA
Emitter cut-off current	I_{EBO}	V_{EB}= -5V , I_C=0			-0.1	μA
DC current gain	h_{FE}	V_{CE}=- 6V, I_C= -1mA	90		600	
Collector-emitter saturation voltage	V_{CE}(sat)	I_C=-100 mA, I_B= -10mA			-0.3	V
Base-emitter voltage	V_{BE}	I_C=-1mA, V_{CE}=-6V			-0.68	V
Transition frequency	f_T	V_{CE}=-6V, I_C= -10mA	180			MHz

CLASSIFICATION OF h_{FE}

Marking	M4	M5	M6	M7
Range	90-180	135-270	200-400	300-600